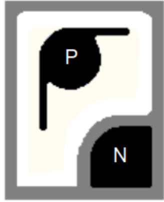

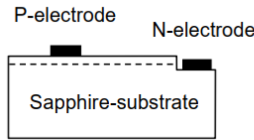

Die Size	233um ± 40um x 183 um ± 40um).
Die Thickness	4.3mil (100um ± 10um)
Bond pad diameter	P: 3mil (75um±10um) N: 2.8mil (70±10um)
Electrode N Metal:	Au alloy
Electrode P Metal:	Au alloy

Absolute Maximum Rating (Ta=25°C)

Parameter	Symbol	Condition	Rating	Unit
DC Forward Current	If	Ta=25°C	≤ 30	mA
DC Reverse Voltage	Vr	Ta=25°C	≤ 5	V
Junction Temperature	Tj	-	≤ 115	°C
Storage Temperature	Tstg	Chip	-40 ~ +85	°C
		Chip-on-tape/storage	5 ~ 35	
		Chip-on-tape/transportation	-20 ~ +65	
Temperature during packaging	-	-	280 (<10sec)	°C

Note: Maximum ratings are package dependent. The above maximum ratings were determined using a Printed Circuit Board (PCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

Electro-Optical Characteristics: (Ta=25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
DC Forward Voltage	VF1	IF=10uA	1.8	-	-	V
	VF2	IF=10mA	-	2.8	3.4	V
DC Reverse Current	IR	VR=5V	-	-	2.0	µA
Domi. Wavelength*2	λd	IF=10mA 2nm/bin	516	-	534	nm
Spectra Half-width	∆λ	IF=10mA	-	35	-	nm
Luminous Intensity*3	IV I28	IF=10mA	460	-	500	mcd
	IV I29	IF=10mA	500	-	550	mcd
	IV I30	IF=10mA	550	-	600	mcd

*1: ESD protection during chip handling is recommended
*2: Basically, the wavelength is 20nm; however, customers´special requirements are also welcome
*3: Lumious intensity is measured by the manufacturer equipment an bare chips.

Typical Electro- Optical Characteristics Curve:

Fig.1 – Relative luminous Intensity vs. Forward Current

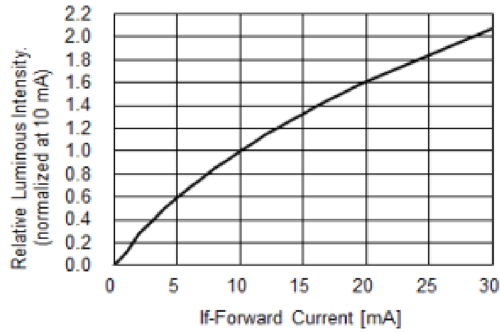

Fig.2 – Forward Current vs. Forward Voltage

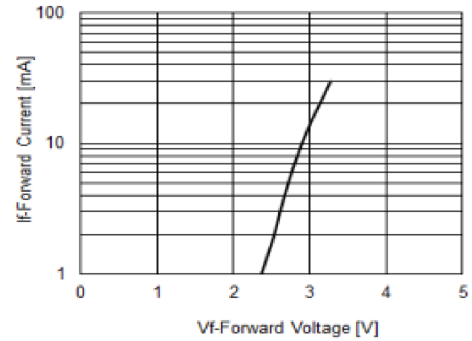

Fig.3 – Relative Intensity (@10mA) vs. Ambient Temperature

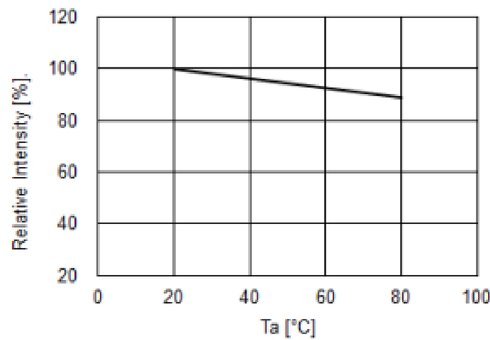

Fig.4 – Forward Voltage (@10mA) vs. Ambient Temperature

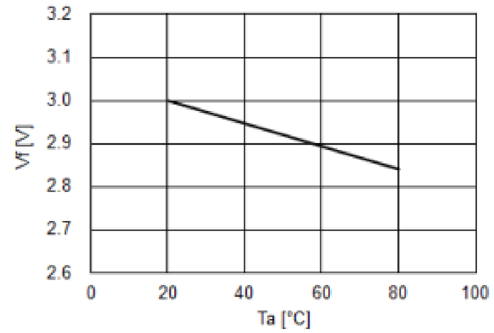

Fig.5 – Dominant Wavelength (@10mA) vs. Ambient Temperature

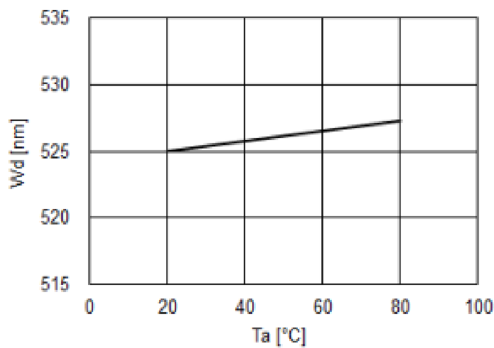

Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on Tj max. = 115°C)